

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 08-181076

(43)Date of publication of application : 12.07.1996

(51)Int.Cl. H01L 21/205

(21)Application number : 07-267076

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(22)Date of filing : 16.10.1995

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(30)Priority

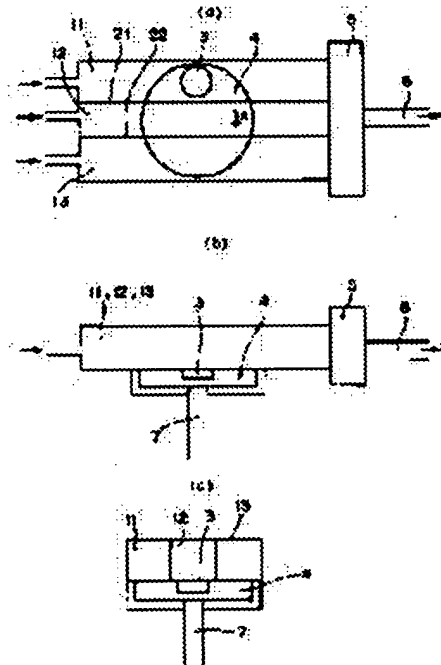
Priority number : 06262699 Priority date : 26.10.1994 Priority country : JP

(54) THIN FILM FORMING METHOD AND DEVICE

(57)Abstract:

PURPOSE: To provide an epitaxial growth method and a vapor growth device through which it is carried out, wherein an atomic growth layer of high quality is grown at a high speed.

CONSTITUTION: Material gases different from each other in content are supplied through gas flow paths 11 and 13 provided inside a reaction oven to form the flows of gases. A substrate 3 is so set as to be movable in parallel with the direction of a gas flow on the same plane with the inner walls of the gas flow paths 11 and 13. A first process wherein the surface of the substrate 3 is introduced into the flow path 11, brought into contact with a flow of gas, and made to adsorb elements contained in it and a second process wherein the surface of the substrate 3 is introduced into the flow path 13, brought into contact with a flow of gas, and made to react on elements contained in it to form an atomic layer thin film are provided, whereby an atomic layer is made to grow through a chemical vapor growth method.



LEGAL STATUS

[Date of request for examination] 17.09.1998

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]